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Stock Code: 301308.SZ

FORESEE®

More than Foresee

EMBEDDED STORAGE PRODUCT CATALOGUE

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PRODUCT LINE INTRODUCTION

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BRAND INTRODUCTION

Embedded Storage Product Line Introduction

The FORESEE embedded storage product line was established in 2011. The first mass-produced eMMC in China was launched the same year. After over 10 years of mutual growth alongside industry clients, FORESEE has released embedded storage products which use Flash, DRAM, or multi-chip packaging. These types of products have become widely used in automotive electronics, industrial control, smartphones, tablets, smart TVs, smart wearables, network communication, and many other fields. FORESEE has also established long-term tight-knit cooperation with Qualcomm, MediaTek, UniSOC, and other chip platform suppliers to provide global enterprises in consumption, industrial, and automotive fields with stable and reliable products.

With Longsys's multiple core patents and in-house firmware, FORESEE embedded storage products have undergone multiple strict verification tests and can comprehensively meet the system smoothness and data stability requirements. Its automotive eMMC has passed AEC-Q100, the reliability standard qualification of the Automotive Electronics Council (AEC) and one of the most credible qualification for the automotive industry.

Technical Features



FBA

The pSLC mode of free blocks is used to boost performance.



Power-loss Protection

Power-loss Protection: Data validity is ensured even when power is turned off or voltage is unstable.



Pre-exchange

Data is replaced before errors occur.



FFU

The cost and difficulty of after-sales services and maintenance are greatly reduced.



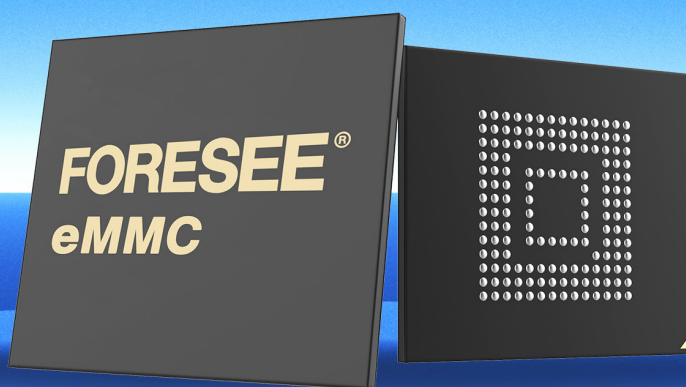
Actively Organizing

The SoC platform can organize data actively to improve the read/write performance.



Enhance Mode

The storage area is enhanced to make key data more secure and reliable.



Applications



Smartphones



tablets



smart TVs



set-top boxes



smart speakers



smart watches



smart cameras



smart bands



smart earphones



car multimedia
entertainment



industrial
automation



IPCs



communication
base stations



Wi-Fi routers



commercial
display devices



streaming
rear-view mirrors



and
dashcams

Automotive eMMC Grade2

Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
4GB	FEMDME004G-A8A39	1.8V/3.3V	pSLC	-40°C to 105°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample
8GB	FEMDME008G-A8A39	1.8V/3.3V	MLC	-40°C to 105°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample
8GB	FEMDME008G-A8A43	1.8V/3.3V	pSLC	-40°C to 105°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample
16GB	FEMDME016G-A8A43	1.8V/3.3V	MLC	-40°C to 105°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample
16GB	FEMDME016G-A8A58	1.8V/3.3V	pSLC	-40°C to 105°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample
32GB	FEMDME032G-A8A58	1.8V/3.3V	MLC	-40°C to 105°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample
64GB	FEMDME064G-A8A58	1.8V/3.3V	MLC	-40°C to 105°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample

Automotive eMMC Grade3

Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
8GB	FEMDMW008G-88A39	1.8V/3.3V	MLC	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
16GB	FEMDMW016G-88A43	1.8V/3.3V	3D NAND	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
32GB	FEMDMW032G-88A19	1.8V/3.3V	3D NAND	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
64GB	FEMDMW064G-88A19	1.8V/3.3V	3D NAND	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production

Industrial Wide-temperature eMMC

Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
8GB	FEMDRW008G-88A39	1.8V/3.3V	MLC	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
16GB	FEMDRW016G-88A43	1.8V/3.3V	MLC	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
32GB	FEMDRW032G-88A19	1.8V/3.3V	3D NAND	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
64GB	FEMDRW064G-88A19	1.8V/3.3V	3D NAND	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
128GB	FEMDRW128G-88A19	1.8V/3.3V	3D NAND	-40°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production

Industrial eMMC

Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
8GB	FEMDRM008G-A3A55	1.8V/3.3V	MLC	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sampling
16GB	FEMDRM016G-A3A55	1.8V/3.3V	MLC	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	New
32GB	FEMDRM032G-A3A55	1.8V/3.3V	3D NAND	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sampling
32GB	FSEIASLD-32G	1.8V/3.3V	3D NAND	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
64GB	FSEIASLD-64G	1.8V/3.3V	3D NAND	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
64GB	FEMDRM064G-A3A56	1.8V/3.3V	3D NAND	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
128GB	FEMDRM0128G-A3A56	1.8V/3.3V	3D NAND	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production
128GB	FSEIASLD-128G	1.8V/3.3V	3D NAND	-25°C to 85°C	eMMC 5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Production

Commercial eMMC

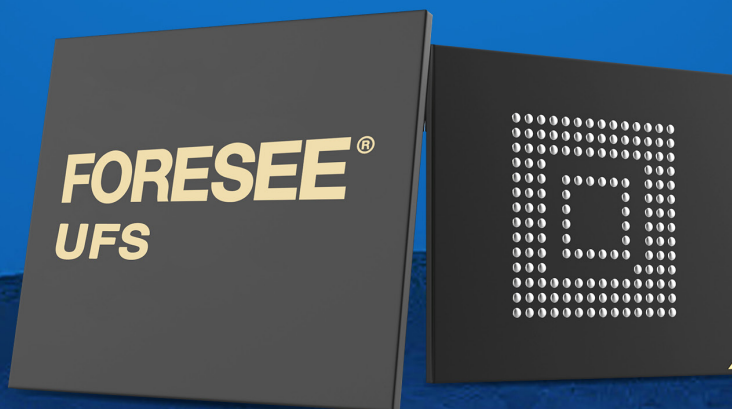
Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
8GB	FEMDNN008G-A3A55	1.8V/3.3V	3D TLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	11.5 x 13 x 0.8 mm	MP
16GB	FEMDNN016G-A3A55	1.8V/3.3V	3D TLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	11.5 x 13 x 0.8 mm	MP
32GB	FEMDNN032G-A3A55	1.8V/3.3V	3D TLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	11.5 x 13 x 0.8 mm	Production
64GB	FEMDNN064G-A3A56	1.8V/3.3V	3D TLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	11.5 x 13 x 0.8 mm	Production
128GB	FEMDNN128G-A3A56	1.8V/3.3V	3D TLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	11.5 x 13 x 0.8 mm	Production
256GB	FEMDNN256G-A3A56	1.8V/3.3V	3D TLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	11.5 x 13 x 1.0 mm	Sample

Commercial Subsize eMMC

Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
4GB	FEMKNN004G-58A42	1.8V/3.3V	MLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	9*7.5*0.8mm	Production
8GB	FEMKNN008G-58A42	1.8V/3.3V	MLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	9*7.5*0.8mm	Sample
32GB	FEMJNM032G-58C29	1.8V/3.3V	TLC	-25°C to 85°C	eMMC5.1	FBGA153	Tray	9*10*0.8mm	Production

Advantages

- eMMCs in various specifications can be used in complex and fluctuating application scenarios to meet clients' strict requirements for high performance, low power consumption, compatibility, and stability.
- Taking the JEDEC pin standards into account, the sub-size eMMC features a smaller size and less PCB space.
- The industrial/industrial wide-temperature/automotive eMMCs comply with the IATF 16949 standard. Boasting a mean time between failures (MTBF) of over 20 million hours, high reliability, and a long service life, they can ensure the around-the-clock operations of devices for extended periods.
- The automotive eMMCs meet the reliability validation standard AEC-Q100.



Applications



Smartphones



smart tablets



smart cameras



VR/AR



cars with a smart-driving system



multimedia entertainment



streaming rear-view mirror



and dashcams

Automotive UFS

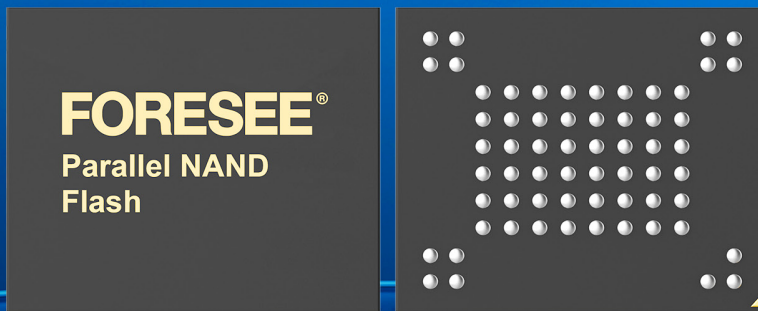
Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
64GB	FEUDME064G-B8A19	1.8V/3.3V	3D NAND	-40 to 105	UFS 2.1 Gear3 2L	FBGA153	Tray	11.5 x 13 x 1.2mm	Sample
128GB	FEUDME128G-B8A19	1.8V/3.3V	3D NAND	-40 to 105	UFS 2.1 Gear3 2L	FBGA153	Tray	11.5 x 13 x 1.2mm	Sample

Commercial UFS

Density	P/N	Voltage	Memory	Temp. Range	Interface	Package	Packing	Size	Status
64GB	FEUDNN064G-C2A56	1.8V/3.3V	3D NAND	-25°C to 85°C	UFS2.2	FBGA153	Tray	11.5 x 13 x 1.0mm	Production
64GB	FEUDNN064G-C2H14	1.8V/3.3V	3D NAND	-25°C to 85°C	UFS2.2	FBGA153	Tray	11.5 x 13 x 1.0mm	Sample
128GB	FEUDNN128G-C2A56	1.8V/3.3V	3D NAND	-25°C to 85°C	UFS2.2	FBGA153	Tray	11.5 x 13 x 1.0mm	Production
128GB	FEUDNN128G-C2H14	1.8V/3.3V	3D NAND	-25°C to 85°C	UFS2.2	FBGA153	Tray	11.5 x 13 x 1.0mm	Sample
256GB	FEUDNN256G-C2A44	1.8V/3.3V	3D NAND	-25°C to 85°C	UFS2.2	FBGA153	Tray	11.5 x 13 x 1.0mm	Production

Advantages

- Large capacity, high performance and lower power consumption ensure longer battery life for devices
- New features of UFS 2.2/UFS 3.1, LDPC algorithm, Write Booster, HPB, emergency power failure protection, FFU upgrade, FBA data acceleration, and other functions are supported.
- Compatible with mainstream platforms
- The automotive UFS meet the reliability validation standard AEC-Q100.
- High reliability and long service life can ensure the around-the-clock operations of devices for extended periods.



Applications



GPON



STBs



IPCs



smart speakers



and drones

Parallel NAND Flash (TSOP)

Density	P/N	Voltage	Memory	Temp. Range	Bus	Package	Packing	Size
1Gb	FS33ND01GS108TFI0	3.3V	SLC	-40°C to 85°C	x8	TSOP48	Tray	12 x 20 x 1.2 mm
1Gb	FSNU8A001G-TWT	1.8V	SLC	-40°C to 85°C	x8	TSOP48	Tray	12 x 20 x 1.2 mm
1Gb	FSNS8A001G-TWT	3.3V	SLC	-40°C to 85°C	x8	TSOP48	Tray	12 x 20 x 1.2 mm
2Gb	FSNU8A002G-TWT	1.8V	SLC	-40°C to 85°C	x8	TSOP48	Tray	12 x 20 x 1.2 mm
2Gb	FSNS8A002G-TWT	3.3V	SLC	-40°C to 85°C	x8	TSOP48	Tray	12 x 20 x 1.2 mm
4Gb	FS33ND04GS108TFI0	3.3V	SLC	-40°C to 85°C	x8	TSOP48	Tray	12 x 20 x 1.2 mm

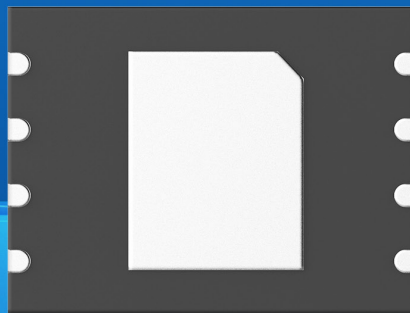
Parallel NAND Flash (BGA)

Density	P/N	Voltage	Memory	Temp. Range	Bus	Package	Packing	Size
1Gb	FSNS8A001G-EWT	3.3V	SLC	-40°C ~ 85°C	x8	BGA48	Tray	8 x 6 x 1.0 mm
2Gb	FSNU8A002G-EWT	1.8V	SLC	-40°C ~ 85°C	x8	BGA48	Tray	8 x 6 x 1.0 mm
4Gb	FS33ND04GS108BFI0	3.3V	SLC	-40°C to 85°C	x8	BGA63	Tray	9 x 11 x 1.0 mm

Advantages

- The mainstream products support 62x2K bytes large-capacity OTP space.
- A minimum BGA package of 48ball 8x6mm is supported to save PCB space.

FORESEE[®] SPI NAND Flash



Applications



GPON



Wi-Fi routers



smart speakers



IPCs



STBs



and video
doorbells

SPI NAND Flash (1.8V)

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size
512Mb	F35UQA512M-WWT	1.8V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	Tray	8 x 6 x 0.8 mm
512Mb	F35UQA512M-VWR	1.8V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	T&R	6 x 5 x 0.8 mm
1Gb	F35UQA001G-WWT	1.8V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	Tray	8 x 6 x 0.8 mm
1Gb	F35UQA001G-VWR	1.8V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	T&R	6 x 5 x 0.8 mm
2Gb	F35UQA002G-WWT	1.8V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	Tray	8 x 6 x 0.8 mm

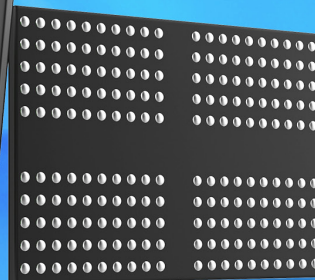
SPI NAND Flash (3.3V)

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size
512Mb	F35SQA512M-WWT	3.3V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	Tray	8 x 6 x 0.8 mm
512Mb	F35SQA512M-VWR	3.3V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	T&R	6 x 5 x 0.8 mm
1Gb	F35SQA001G-WWT	3.3V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	Tray	8 x 6 x 0.8 mm
1Gb	F35SQA001G-VWR	3.3V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	T&R	6 x 5 x 0.8 mm
2Gb	F35SQA002G-WWT	3.3V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	Tray	8 x 6 x 0.8 mm
4Gb	FS35ND04G-S2Y2QWF1000	3.3V	SLC	-40°C to 85°C	x1/x2/x4	SPI	WSO8	Tray	8 x 6 x 0.8 mm

Advantages

- The product is equipped with a general-purpose SPI and internal error correcting code (ECC) to improve data transmission efficiency and ensure data reliability.
- A minimum WSON 6mm*5mm package is supported to save PCB space.
- As the first 512Mb SPI NAND Flash product in mainland China, it comes with optimized wafer design, helping clients reduce the costs of complete machine systems while also making their products more competitive.

FORESEE® LPDDR4x



Applications



Smartphones



tablets



smart TVs



STBs



smart speakers



dash cams



and smart cameras

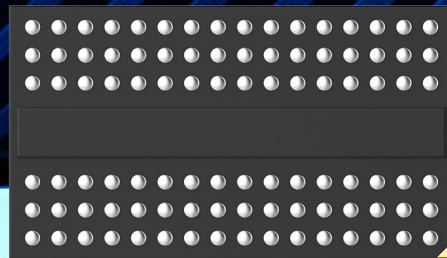
LPDDR4x

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size	Status
8Gb	NCLDXC1MG256M32	1.8V/1.1V/1.1V or 0.6V	1nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
16Gb	FLXC2002G-N2	1.8V/1.1V/1.1V or 0.6V	10nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
16Gb	FLXC2002G-C4	1.8V/1.1V/0.6V	1nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
24Gb	FLXC2003G-49	1.8V/1.1V/1.1V or 0.6V	12nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
24Gb	FLXC2003G-C7	1.8V/1.1V/ 0.6V	12nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
24Gb	FLXC4003G-50	1.8V/1.1V/1.1V or 0.6V	1xnm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
32Gb	FLXC2004G-30	1.8V/1.1V/1.1V or 0.6V	10nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
32Gb	FLXC2004G-N1	1.8V/1.1V/1.1V or 0.6V	10nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
48Gb	FLXC4006G-20	1.8V/1.1V/1.1V or 0.6V	12nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	Production
64Gb	FLXC4008G-30	1.8V/1.1V/1.1V or 0.6V	10nm	-25°C to 85°C	x32	LPDDR4x	FBGA200	Tray	10*14.5*1.0mm	New

Advantages

- RAM products that are widely used for portable devices
- Improves performance and reduces system power consumption.

FORESEE® DDR3L



Applications



Drones



home IPCs



industrial IPCs



STBs



smart speakers



smart TVs



GPON



POS machines



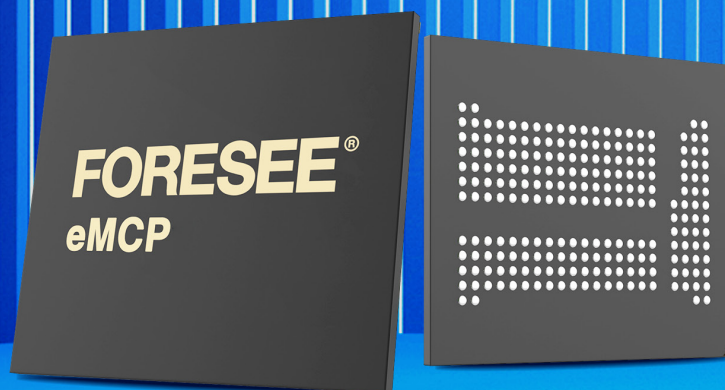
and TV boxes

DDR3L

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size
2Gb	F60C1A0002-M6AR	1.35 or 1.5V	DDR3L	0°C to 95°C	x16	DDR3	FBGA96	Tray	7.5 × 13.5 × 1.2 mm
2Gb	F60C1A0002-M69W	1.35 or 1.5V	DDR3L	-40°C to 95°C	x16	DDR3	FBGA96	Tray	7.5 × 13.5 × 1.2 mm
4Gb	F60C1A0004-M79R	1.35 or 1.5V	DDR3L	0°C to 95°C	x16	DDR3	FBGA96	Tray	7.5 × 13.5 × 1.2 mm
4Gb	F60C1A0004-M79W	1.35 or 1.5V	DDR3L	-40°C to 95°C	x16	DDR3	FBGA96	Tray	7.5 × 13.5 × 1.2 mm

Advantagess

- It adopts the 25nm process and complies with JEDEC standards.
- The product meets the data caching demands of network communication, consumer electronics, and smart devices.



Applications



eMCP3

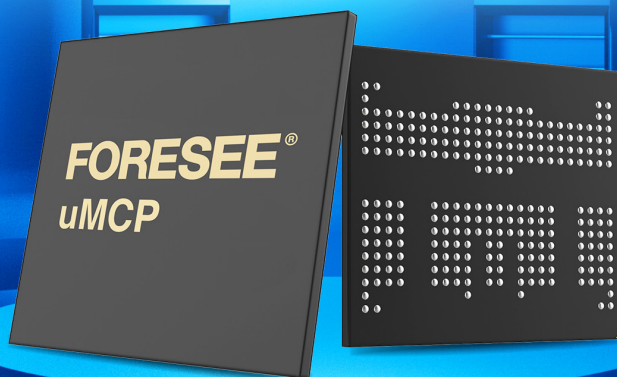
Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size	Status
16GB+8Gb	FEPNA1608-58A4302	1.8V/3.3V	MLC+20nm	-25°C to 85°C	x8+ x32	eMCP3	FBGA221	Tray	11.5 x 13 x 1.0 mm	Production
16GB+8Gb	FEPNA1608-58A4324	1.8V/3.3V	MLC+20nm	-25°C to 85°C	x8+ x32	eMCP3	FBGA221	Tray	11.5 x 13 x 1.0 mm	Production
32GB+8Gb	FEPNA3208-58A1924	1.8V/3.3V	3D NAND+20nm	-25°C to 85°C	x8+ x32	eMCP3	FBGA221	Tray	11.5 x 13 x 1.0 mm	Production

eMCP4x

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size	Status
64GB+32Gb	FEPRF6432-58A1930	eMMC:1.8V/3.3V LPDDR: 1.8V/1.1/1.1or 0.6	3D NAND+12nm	-25°C to 85°C	x8+ x32	eMCP4x	FBGA254	Tray	11.5 x 13 x 1.0 mm	Production
64GB+32Gb	FEPRB6432-A3A56N1	eMMC:1.8V/3.3V LPDDR: 1.8V/1.1/1.1or 0.6	3D NAND+12nm	-25°C to 85°C	x8+ x32	eMCP4x	FBGA254	Tray	11.5 x 13 x 1.0 mm	Production
128GB+32Gb	FEPRFA832-A3A56N1	eMMC:1.8V/3.3V LPDDR: 1.8V/1.1/1.1or 0.6	3D NAND+12nm	-25°C to 85°C	x8+ x32	eMCP4x	FBGA254	Tray	11.5 x 13 x 1.0 mm	Production

Advantagess

- Combines eMMC and LPDDR
- Saves PCB space, enabling compact and lightweight smart devices.
- eMMC and LPDDR are integrated and packaged with precision to provide unique ECC, CRC, power failure protection, firmware backup, balanced wear, and more.
- It can effectively help clients boost usage efficiency, reduce usage costs, improve storage experience, and enhance product continuity and stability.



Applications



Smartphones



smart tablets



high-end
smart TVs



high-end commercial
display devices



VR/AR



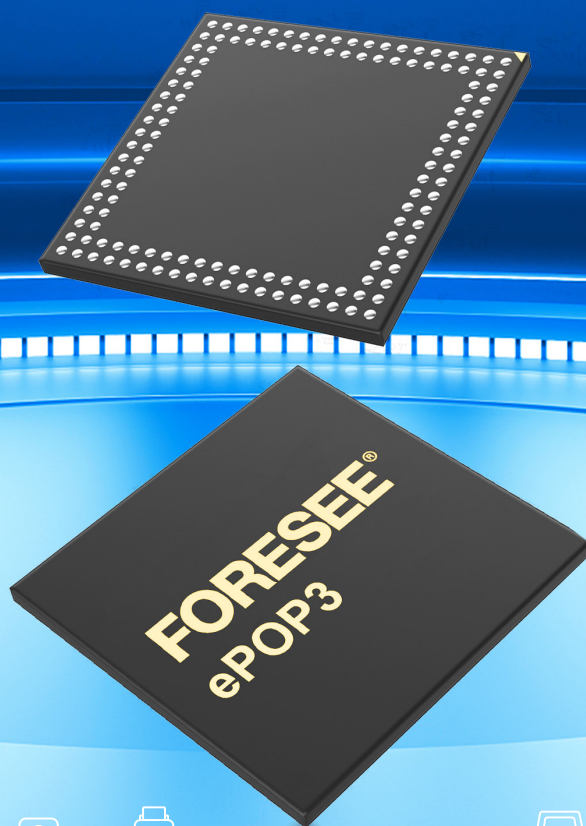
and smart
cameras

uMCP

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size
64GB+ 32Gb	FUPRB6432-C2A56N1	UFS:1.8V/3.3V LPDDR: 1.8V/1.1/1.1or 0.6	3D NAND+ 1nm	-25°C to 85°C	x8+ x32	uMCP4x	FBGA254	Tray	11.5 x 13 x 1.0 mm
128GB+ 32Gb	FUPRFA832-C2A56N1	UFS:1.8V/3.3V LPDDR: 1.8V/1.1/1.1or 0.6	3D NAND+ 1nm	-25°C to 85°C	x8+ x32	uMCP4x	FBGA254	Tray	11.5 x 13 x 1.0 mm

Advantagess

- LPDDR and UFS are combined to enable high performance and large capacity. Compared with distributed storage solutions, it takes up 40% less PCB space.
- The PCB space of memory chips is reduced to enable more flexible system designs.
- Enabling high-density and low power consumption storage solutions for smartphone and smart device designs



Applications



Smart teaching tablets



wearables



smart speakers



children's watches



dash cams



Smart TVs



commercial smart TVs



STBs



and communication base stations

ePOP3

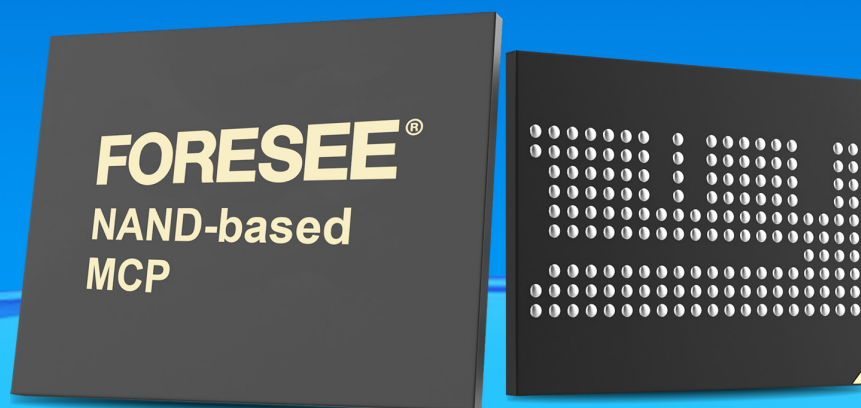
Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size
8GB+4Gb	FAPUA0804-58C2948	1.8V/3.3V+1.2V	3D NAND+20nm	-25°C to 85°C	x8+ x32	ePOP3	FBGA136	Tray	10*10*0.9mm
8GB+8Gb	FAPUB0808-58C2948	1.8V/3.3V+1.2V	3D NAND+20nm	-25°C to 85°C	x8+ x32	ePOP3	FBGA136	Tray	10*10*0.9mm
32GB+8Gb	FAPUB3208-58C2948	1.8V/3.3V+1.2V	3D NAND+20nm	-25°C to 85°C	x8+ x32	ePOP3	FBGA136	Tray	10*10*0.9mm

ePOP4x

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size
32GB+16Gb	FAPEA3216-58C29N3	1.8V/3.3V+0.6V	3D NAND+1nm	-25°C to 85°C	x8+ x16	ePOP4x	FBGA144	Tray	8*9.5*0.8mm

Advantagess

- Integrating eMMC and LPDDR, this compound product is tailor-made for wearables.
- Compared with eMCP products, it is thinner, smaller, and consumes less energy.



Applications



MIFI



POS machines



feature phones



4G modules



and children's watches

nMCP

Density	P/N	Voltage	Memory	Temp. Range	Bus	Interface	Package	Packing	Size	Status
1Gb+1Gb	F70ME0101D-RDWA	1.8V	SLC+LP2	-40°C to 85°C	x8 + x32	LPDDR2	BGA162	Tray	8 x 10.5 x 1.0mm	Production

优势

- Flash and LPDDR are packaged in a single package to simplify wiring design and save space.
- A core voltage of 1.8V can meet the low power consumption requirements of wearable devices and the Internet of Things (IoT).

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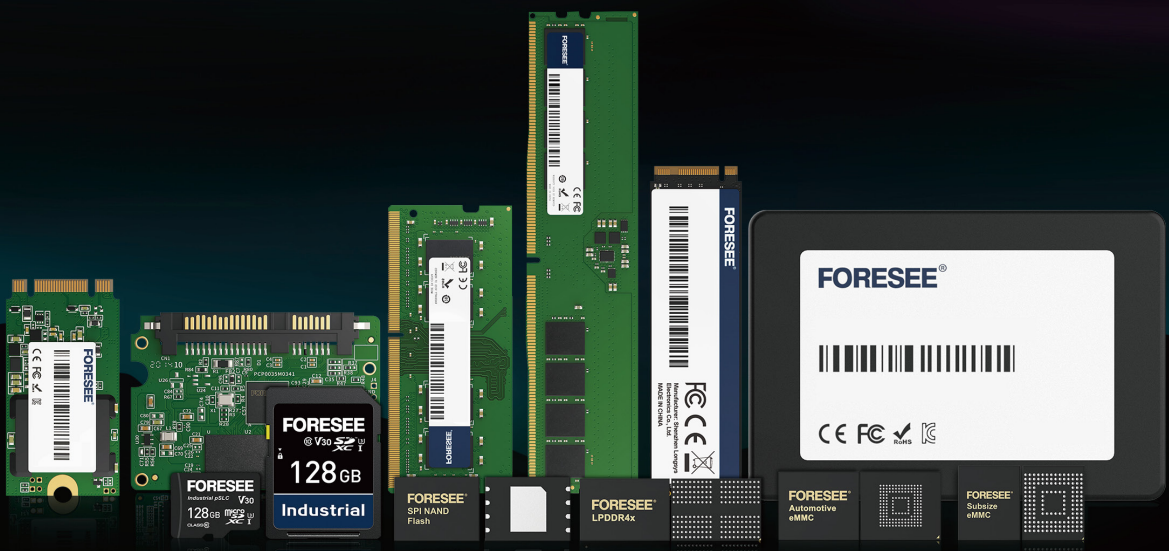
The actual products shall always prevail.

The data comes from internal tests of Longsys. The actual performance may vary due to equipment differences.

About FORESEE

Founded in 2011, FORESEE has burgeoned into a storage brand specializing in industrial applications. Powered by technology, focused on customers, and driven by innovation, FORESEE has been engaged in the storage industry for many years. It owns four product lines: embedded storage (including industrial storage), mobile memory, solid-state drive, and memory module.

FORESEE has made continuous efforts in independent R&D as well as comprehensive quality control. It also develops new products based on industry dynamics and market needs to optimize performance, expand storage capacity, reduce power consumption, and improve overall quality. FORESEE also provides professional and instantaneous technical support and market services. FORESEE is capable of providing industrial-grade storage product solutions, also prides itself in taking advantage of its ample delivery experience to provide customers with effective, innovative, and quality storage products and solutions. In addition, FORESEE has established long-term, stable, and in-depth cooperative relationships with high-end customers in many industries. As a brand with industry-oriented values and a strong sense of responsibility, FORESEE will continue to bolster its competitiveness edge within the storage industry. FORESEE will offer cutting-edge and high-quality technologies and superior services to empower not only the various application innovation and future storage development fields, but also the entire industry.



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